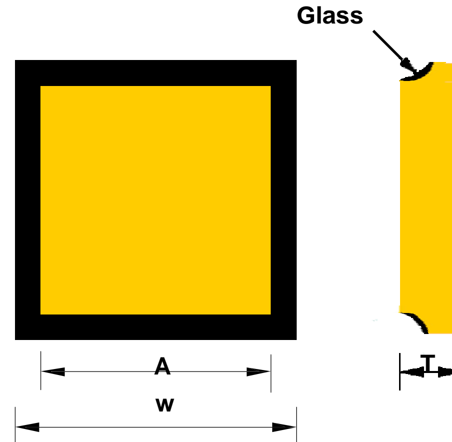
DGS84 THRU DGS100

General Purpose Rectifier GPP Chips

Features

- **Fully glass passivated-needs no encapsulation**
- **Peak reverse voltage to 1800 volts**
- **Low forward voltage drop(VF)**
- **Metallized surface**



Description

The GPP chips series are diffused silicon, glass passivated rectifier die.

These devices can be supplied to meet customer's requirements.

The prime application for unencapsulated die is in hybrid circuits. For this reason, a variety of metallized surfaces are available.

Gold is standard for wire bonding, and for soldering application, gold flash chips are supplied.

Electrical Characteristics (T_a = 25°C unless specified)

PAR AMETER	SYMBOL	DGS84	DGS88	DGS90	DGS95	DGS100	UNIT
Dimension	W	84±3	88±3	90±3	95±3	100±3	mils
Dimension	A	71±3	75±3	76±3	81±3	87±3	mils
Dimension	T	265±8					µm
Peak Inverse Voltage	V_B	1100					Volts
Forward current	I_F	3.0	3.0	3.0~5.0	3.0~5.0	3.0~5.0	Amps
Forward Voltage Drop	V_F	≤ 0.98	≤ 0.98	≤ 0.98	≤ 0.98	≤ 0.98	Volts
Forward Surge current	I_{FSM}	120	120	120	120	120	Amps
Reverse Recovery Time	T_{RR}	≥ 1000	≥ 1000	≥ 1000	≥ 1000	≥ 1000	ns
Junction Temperature	T_{JFM}	175	175	175	175	175	°C
Reverse Current at 25 °C	I_R	2	2	2	2	2	µA
Storage Temperature	T_{ST}	-65 --- 175					°C
Die attach Temperatu re	T_d	375					°C

Note :

Other dimension of GPP chip ranging from 42 mils to 600 mils which is not specified on the list, can also be supplied by special procurement agreement.